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(54) Title: METHOD TO ELIMINATE FIRST WAFER EFFECTS ON SEMICONDUCTOR PROCESS CHAMBERS

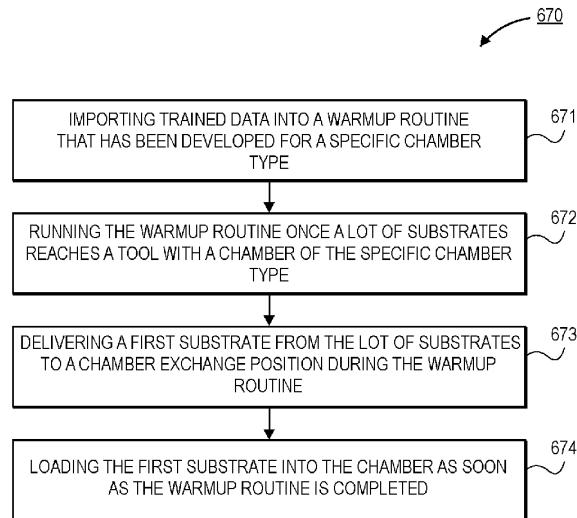


FIG. 6

(57) Abstract: Embodiments disclosed herein include methods for monitoring chamber performance in order to mitigate first wafer effects. In an embodiment, a method for determining an optimum chamber condition comprises monitoring a parameter during execution of a recipe for a number of substrates after the chamber has been in an idle state. In an embodiment, the method further comprises determining when a repeatability of the parameter meets a stability specification. In an embodiment, the method may continue with recording the parameter.

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